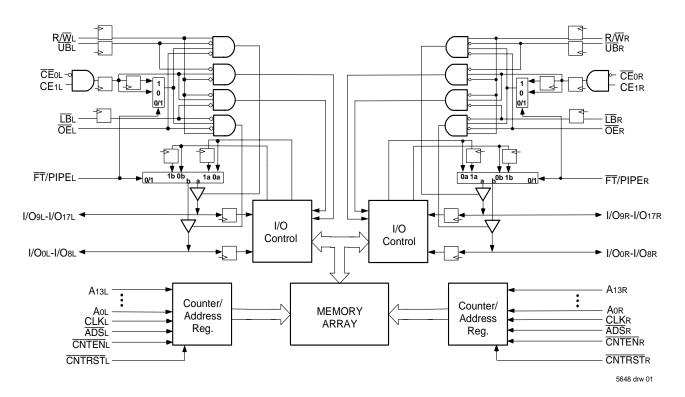
HIGH-SPEED 3.3V 16K x 18 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 6/7.5/9/12ns (max.)
 - Industrial: 7.5ns (max.)
- Low-power operation
 - IDT70V9369L
 Active: 500mW (typ.)
 Standby: 1.5mW (typ.)
- Flow-Through or Pipelined output mode on either port via the FT/PIPE pins
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic

- Full synchronous operation on both ports Ans solution to clock and Ons hold on all contri-
 - 4ns setup to clock and Ons hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 6.5ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 12ns cycle time, 83MHz operation in Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100-pin Thin Quad Flatpack (TQFP)
- Green parts available, see ordering information



Functional Block Diagram

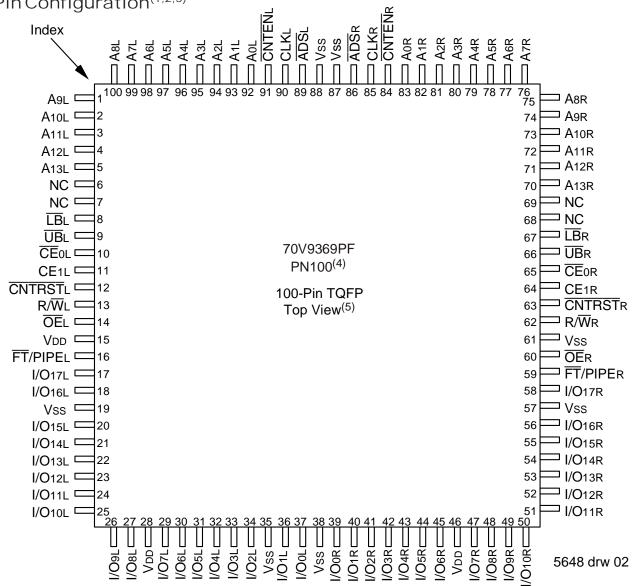
FEBRUARY 2018

Industrial and Commercial Temperature Ranges

Description:

The IDT70V9369 is a high-speed 16K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT70V9369 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using CMOS high-performance technology, these devices typically operate on only 500mW of power.



Pin Configuration^(1,2,3)

- All VDD pins must be connected to power supply. 1.
- All Vss pins must be connected to ground. 2
- Package body is approximately 14mm x 14mm x 1.4mm. 3.
- This package code is used to reference the package diagram. 4
- This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names
CE0L, CE1L	CEOR, CE1R	Chip Enables ⁽²⁾
R/WL	R/Wr	Read/Write Enable
ŌĒL	0E r	Output Enable
Aol - A13l	Aor - A13r	Address
I/O0L - I/O17L	I/Oor - I/O17r	Data Input/Output
CLKL	CLKR	Clock
UBL	UB R	Upper Byte Select ⁽¹⁾
LB L	LB R	Lower Byte Select ⁽¹⁾
ADSL	ADSR	Address Strobe Enable
	CNTEN R	Counter Enable
CNTRSTL	CNTRST R	Counter Reset
FT/PIPEL	FT/PIPER	Flow-Through / Pipeline
V	DD	Power (3.3V)
V	SS	Ground (0V)

5648 tbl 01

NOTES:

1. LB and UB are single buffered regardless of state of FT/PIPE.

 CEoand CE1 are single buffered when FT/PIPE = VIL,
 CEoand CE1 are double buffered when FT/PIPE = VIL, i.e., the signals take two cycles to deselect.

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	CE 0	CE1	ŪB	ΓB	R/W	Upper Byte I/O9-17 ⁽⁴⁾	Lower Byte I/O ₀₋₈ ⁽⁵⁾	MODE
Х	\uparrow	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	\uparrow	Х	L	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	\uparrow	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	\uparrow	L	Н	L	Н	L	DATAIN	High-Z	Write to Upper Byte Only
Х	\uparrow	L	Н	Н	L	L	High-Z	DATAIN	Write to Lower Byte Only
Х	\uparrow	L	Н	L	L	L	DATAIN	DATAIN	Write to Both Bytes
L	\uparrow	L	Н	L	Н	Н	DATAOUT	High-Z	Read Upper Byte Only
L	\uparrow	L	Н	Н	L	Н	High-Z	DATAOUT	Read Lower Byte Only
L	\uparrow	L	Н	L	L	Н	DATAOUT	DATAOUT	Read Both Bytes
Н	Х	L	Н	L	L	Х	High-Z	High-Z	Outputs Disabled

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care. 2. \overline{ADS} , \overline{CNTEN} , \overline{CNTRST} = X.

3. OE is an asynchronous input signal.

5648 tbl 02

Industrial and Commercial Temperature Ranges

Truth Table II—Address Counter Control^(1,2,6)

Address	Previous Internal Address	Internal Address Used	CLK ⁽⁶⁾	ADS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
An	Х	An	\uparrow	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
Х	An	An + 1	\uparrow	Н	L ⁽⁵⁾	Н	D⊮o(n+1)	Counter Enabled—Internal Address generation
х	An + 1	An + 1	\uparrow	Н	Н	Н	D⊮o(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
х	Х	A0	\uparrow	Х	Х	L ⁽⁴⁾	Dı/o(0)	Counter Reset to Address 0

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{CE}_0 , \overline{LB} , \overline{UB} , and $\overline{OE} = VIL$; CE1 and R/ $\overline{W} = VIH$.

3. Outputs configured in Flow-Through Output mode; if outputs are in Pipelined mode the data out will be delayed by one cycle.

4. ADS and CNTRST are independent of all other signals including CEo, CE1, UB and LB.

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CE0, CE1, UB and LB.

6. While an external address is being loaded (ADS = VIL), R/W = VIH is recommended to ensure data is not written arbitrarily.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature ⁽¹⁾	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V
			5648 tbl 04

NOTE:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vdd	Supply Voltage	3.0	3.3	3.6	V
Vss	Ground	0	0	0	V
V⊪	Input High Voltage	2.0V	_	VDD+0.3V ⁽²⁾	V
Vil	Input Low Voltage	-0.3(1)		0.8	V

NOTES:

1. $V_{IL} \ge -1.5V$ for pulse width less than 10 ns.

2. VTERM must not exceed V_{DD} +0.3V.

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
Tbias ⁽³⁾	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
ЛЛ	Junction Temperature	+150	٥C
lout	DC Output Current	50	mA
	-		5648 tbl 06

Absolute Maximum Ratings⁽¹⁾

NOTES:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed VDD +0.3V.

3. Ambient Temperature Under DC Bias. No AC Conditions. Chip deselect.

Capacitance⁽¹⁾ (TA = $+25^{\circ}$ C, f = 1 0MHz)

Symbol	Parameter	Conditions	Мах.	Unit
Cin	Input Capacitance	VIN = 0V	9	pF
Cout ⁽²⁾	Output Capacitance	Vout = 0V	10	pF

NOTES:

1. These parameters are determined by device characterization, but are not production tested. 2. Court also references CI/O.

5648 tbl 03

5648 tbl 05

5648 tbl 07

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($V_{DD} = 3.3V \pm 0.3V$)

				70V9369L		
Symbol	Parameter	Test Conditions	Min.	Мах.	Unit	
LL	Input Leakage Current ⁽¹⁾	$V_{DD} = 3.6V$, $V_{IN} = 0V$ to V_{DD}	—	5	μA	
Ilo	Output Leakage Current	\overline{CE} o = VIH or CE1 = VIL, VOUT = 0V to VDD	—	5	μA	
Vol	Output Low Voltage	IoL = +4mA	—	0.4	V	
Vон	Output High Voltage	IOH = -4mA	2.4	-	V	

NOTE:

1. At $V_{DD} \le 2.0V$ input leakages are undefined.

5648 tbl 08

5648 tbl 09

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽³⁾ ($V_{DD} = 3.3V \pm 0.3V$)

						369L6 I Only	Co	369L7 om'l Ind		369L9 I Only		869L12 I Only	
Symbol	Parameter	Test Condition	Versio	n	Typ. ⁽⁴⁾	Мах.	Тур. ⁽⁴⁾	Max.	Тур. ⁽⁴⁾	Мах.	Typ. ⁽⁴⁾	Max.	Unit
lod	Dynamic Operating Current (Both	CEL and CER= VIL,	COM'L	L	220	350	200	290	180	225	150	205	mA
	Ports Active)	Outputs Disabled, $f = fMAX^{(1)}$	IND	L			200	335				_	
ISB1	Standby Current (Both Ports - TTL	$\overline{CE}L = \overline{CE}R = VIH$	COM'L	L	70	130	65	100	50	65	40	50	mA
	Level Inputs)	$f = fMAX^{(1)}$	IND	L			65	115					
ISB2	Standby	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁵⁾	COM'L	L	150	250	140	210	110	150	100	140	mA
	Current (One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	L	_		140	240	_	_	_		
ISB3	Full Standby	Both Ports \overline{CE}_{L} and $\overline{CE}_{R} > V_{DD} - 0.2V$,	COM'L	L	0.4	5	0.4	5	0.4	5	0.4	5	mA
	Current (Both Ports - CMOS Level Inputs)	$VIN \ge VDD - 0.2V$, $VIN \ge VDD - 0.2V$ or $VIN \le 0.2V$, $f = 0^{(2)}$	IND	L			0.4	15				-	
ISB4	Full Standby	\overline{CE} "A" $\leq 0.2V$ and	COM'L	L	140	240	130	200	100	140	90	130	mA
	Current (One Port - CMOS Level Inputs)	$\begin{array}{l} \hline CE^*B^* \stackrel{>}{\geq} V_{DD} - 0.2V^{(5)} \\ VIN \stackrel{>}{\geq} V_{DD} - 0.2V \text{ or} \\ VIN \stackrel{<}{\leq} 0.2V, \text{ Active Port,} \\ Outputs Disabled, f = fMAX^{(1)} \end{array}$	IND	L			130	230	_	_			

NOTES:

1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f=0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. $V_{DD} = 3.3V$, $T_A = 25^{\circ}C$ for Typ, and are not production tested. IDD Dc(f=0) = 90mA (Typ).

5. $\overline{CE}x = VIL \text{ means } \overline{CE}0x = VIL \text{ and } CE1x = VIH$

 $\overline{CE}x = VIH means \overline{CE}ox = VIH or CE1x = VIL$

 $\begin{array}{c} \overline{CE}x \leq 0.2V \text{ means } \overline{CE}_{02} \leq 0.2V \text{ and } CE_{1X} \geq V_{DD} - 0.2V \\ \overline{CE}x \geq V_{DD} - 0.2V \text{ means } \overline{CE}_{0X} \geq V_{DD} - 0.2V \text{ or } CE_{1X} \leq 0.2V \\ \end{array}$

"X" represents "L" for left port or "R" for right port.

Industrial and Commercial Temperature Ranges

AC Test Conditions

no rest conditions	
Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

5648 tbl 10

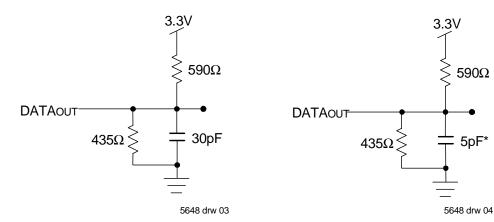
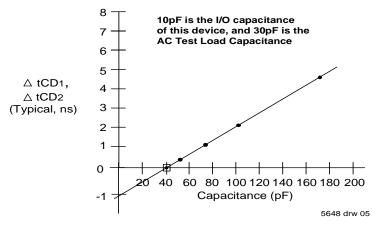


Figure 2. Output Test Load (For tcкLz, tcкHz, toLz, and toHz). *Including scope and jig.





 $\label{eq:Figure 3.} Figure \, 3. \, Typical \, Output \, Derating \, (Lumped \, Capacitive \, Load).$

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)⁽³⁾ ($V_{DD} = 3.3V \pm 0.3V$)

		70V9 Com	9369L6 'I Only	70V9 Com &	369L7 I Only Ind	70V9369L9 Com'l Only		70V9369L12 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Мах.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	19		22	—	25	_	30	_	ns
tCYC2	Clock Cycle Time (Pipelined) ⁽²⁾	10		12	_	15		20	_	ns
tCH1	Clock High Time (Flow-Through) ⁽²⁾	6.5		7.5	—	12	—	12	_	ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	6.5		7.5	—	12	_	12	_	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	4		5	—	6	_	8	_	ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	4		5	—	6	_	8	_	ns
tR	Clock Rise Time	—	3	_	3	-	3	_	3	ns
tr	Clock Fall Time		3	-	3	_	3		3	ns
t SA	Address Setup Time	3.5		4	—	4	—	4	_	ns
tha	Address Hold Time	0		0	—	1		1		ns
tsc	Chip Enable Setup Time	3.5		4	—	4		4		ns
tнc	Chip Enable Hold Time	0		0	—	1		1		ns
tsw	R/W Setup Time	3.5		4		4		4		ns
thw	R/W Hold Time	0		0		1		1		ns
tsp	Input Data Setup Time	3.5		4		4		4		ns
thd	Input Data Hold Time	0		0		1		1		ns
tsad	ADS Setup Time	3.5		4		4		4		ns
thad	ADS Hold Time	0		0		1	—	1	_	ns
tscn	CNTEN Setup Time	3.5		4		4		4		ns
THCN	CNTEN Hold Time	0		0		1	—	1		ns
t SRST	CNTRST Setup Time	3.5		4	_	4		4		ns
thrst	CNTRST Hold Time	0		0		1		1		ns
toe	Output Enable to Data Valid	—	6.5		7.5		9		12	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2		2	_	2	_	2		ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾		15		18	_	20	_	25	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾	_	6.5		7.5	_	9		12	ns
tDC	Data Output Hold After Clock High	2		2	_	2		2		ns
tскнz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2		2	—	2		2		ns
Port-to-Port D	Delay	•	-							•
tcwdd	Write Port Clock High to Read Data Delay	—	24		28		35		40	ns
tccs	Clock-to-Clock Setup Time		9		10	_	15		15	ns

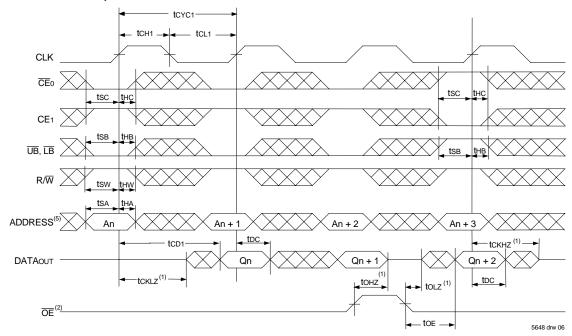
NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

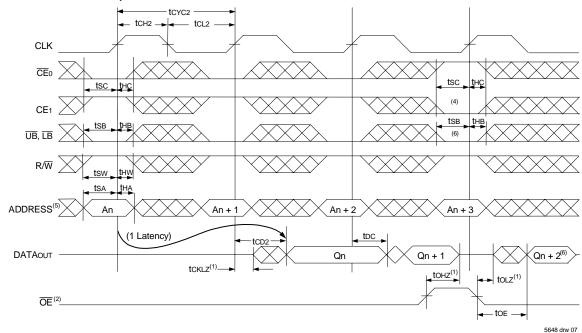
2. The Pipelined output parameters (tcyc2, tcp2) apply to either or both the Left and Right ports when FT/PIPE = VIH. Flow-through parameters (tcyc1, tcp1) apply when FT/PIPE = VIL for that port.

3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER, and FT/PIPEL.

Timing Waveform of Read Cycle for Flow-Through Output $(\overline{FT}/PIPE^*X^* = VIL)^{(3,7)}$



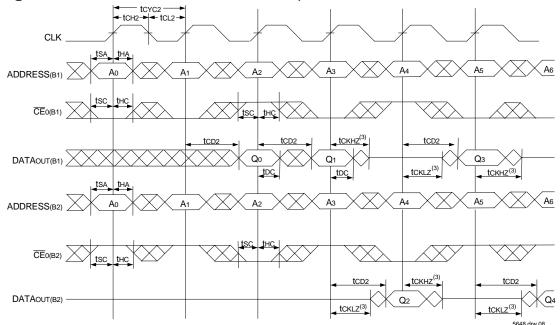
Timing Waveform of Read Cycle for Pipelined Operation $(FT/PIPE"x" = VIH)^{(3,7)}$



- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. ADS = VIL and CNTRST = VIH.
- 4. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{H}$, $\overline{CE}_1 = V_{IL}$, $\overline{UB} = V_{H}$, or $\overline{LB} = V_{H}$ following the next rising edge of the clock. Refer to Notes under Pin Names Table.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
- are for reference use only.
- 6. If UB or LB was HIGH, then the Upper Byte and/or Lower Byte of DATAout for Qn + 2 would be disabled (High-Impedance state).
- 7. "X' here denotes Left or Right port. The diagram is with respect to that port.

Industrial and Commercial Temperature Ranges

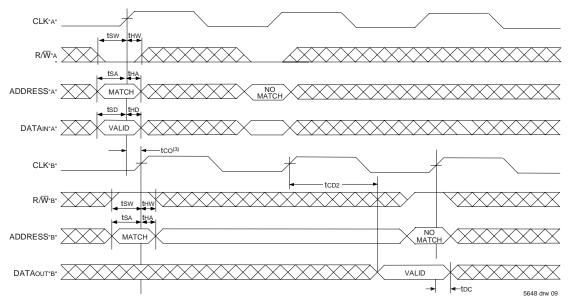
Timing Waveform of a Bank Select Pipelined Read^(1,2)



NOTES:

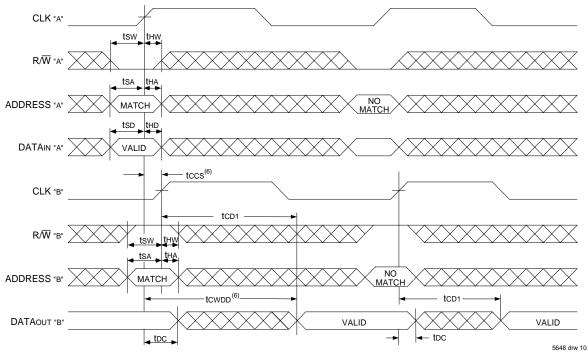
- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9369 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W and \overline{CNTRST} = VIH. 2
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- \overline{CE}_0 , \overline{UB} , \overline{LB} , and $\overline{ADS} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$. 4
- $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to. 5.
- 6. If tccs < maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb.
- If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpp does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

Timing Waveform of Left Port Write to Pipelined Right Port Read^(1,2,4)



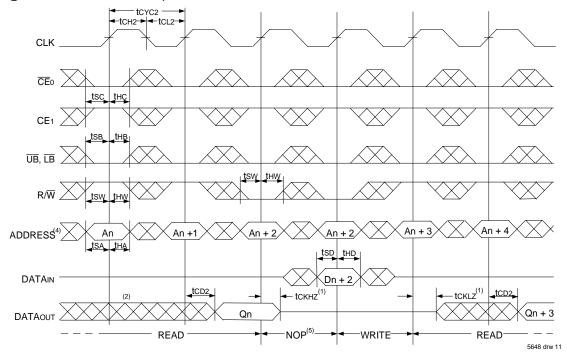
- 1. \overline{CE}_{0} , \overline{BE}_{n} , and $\overline{ADS} = VIL$; CE1 and $\overline{REPEAT} = VIH$.
- 2. $\overline{OE} = V_{IL}$ for Port "B", which is being read from. $\overline{OE} = V_{IH}$ for Port "A", which is being written to.
- If tco < minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco 3. > minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc2 + tcyc2).
- All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A" 4

Timing Waveform with Port-to-Port Flow-Through Read^(4,5,7)

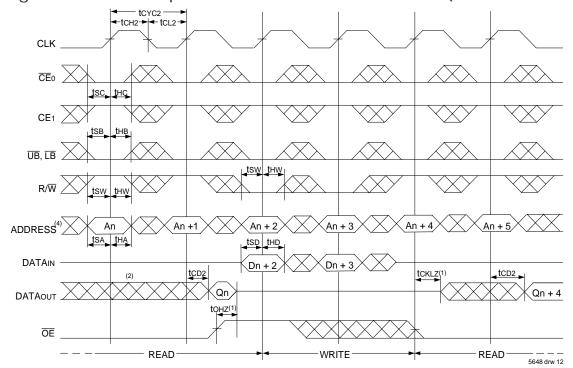


- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9369 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. $\overline{CE}_{0}, \overline{UB}, \overline{LB}, \text{ and } \overline{ADS} = VIL; CE1 \text{ and } \overline{CNTRST} = VIH.$
- 5. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- 6. If tccs < maximum specified, then data from right port READ is not valid until the maximum specified for tcwpd.
- If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpp does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾

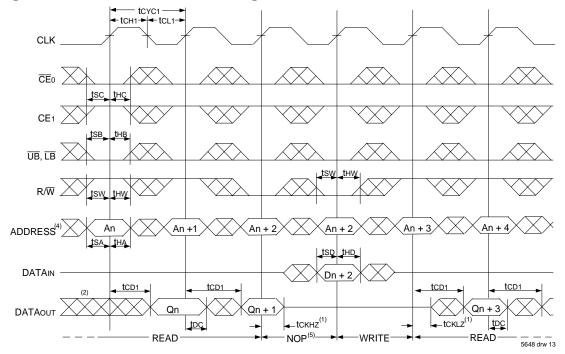


Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽³⁾

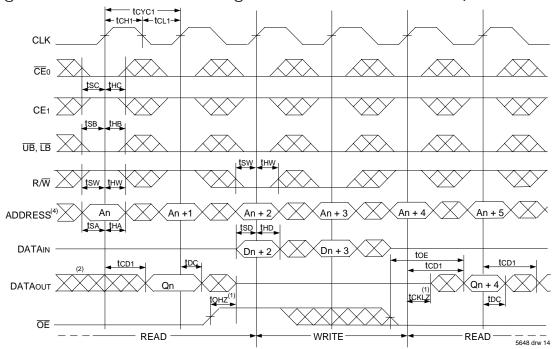


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1 and \overline{CNTRST} = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾

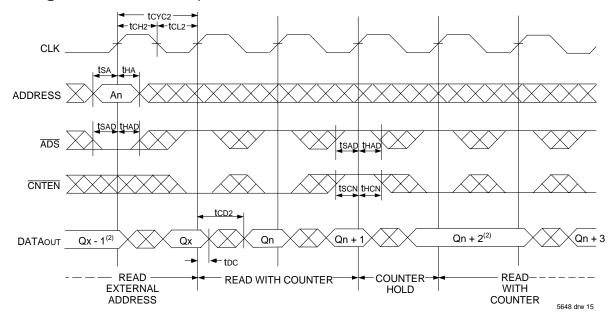


Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽³⁾

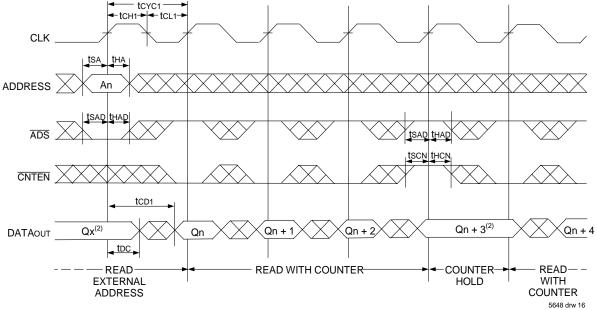


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. CEO, UB, LB, and ADS = VIL; CE1 and CNTRST = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



Timing Waveform of Flow-Through Read with Address Counter Advance $^{(1)}$

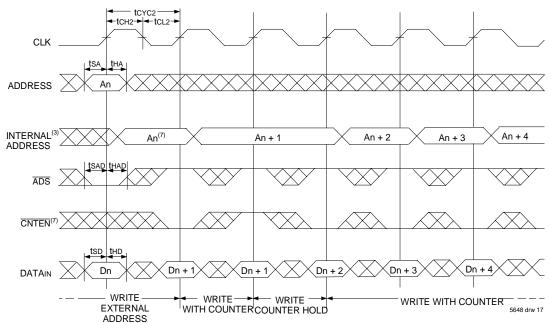


NOTES:

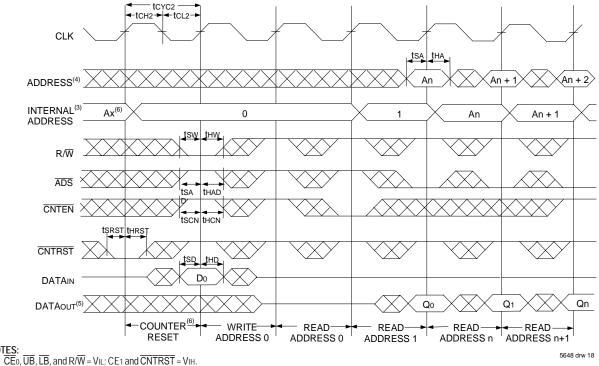
1. $\overline{CE}_{0}, \overline{OE}, \overline{UB}, \text{ and } \overline{LB} = V_{IL}; CE_{1}, R/\overline{W}, \text{ and } \overline{CNTRST} = V_{IH}.$

2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)⁽²⁾



1. \overline{CE}_{0} , \overline{UB} , $\overline{LB} = VIL$; $CE_{1} = VIH$. 2.

- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only. 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle. ADDRo will be accessed. Extra cycles are shown here simply for 6. clarification.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written to during this cycle.

IDT70V9369L

High-Speed 3.3V 16K x 18 Dual-Port Synchronous Pipelined Static RAM

Functional Description

The IDT70V9369 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

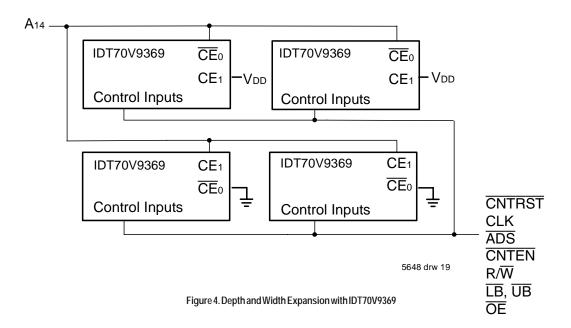
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to staff the operation of the address counters for fast interleaved memory applications.

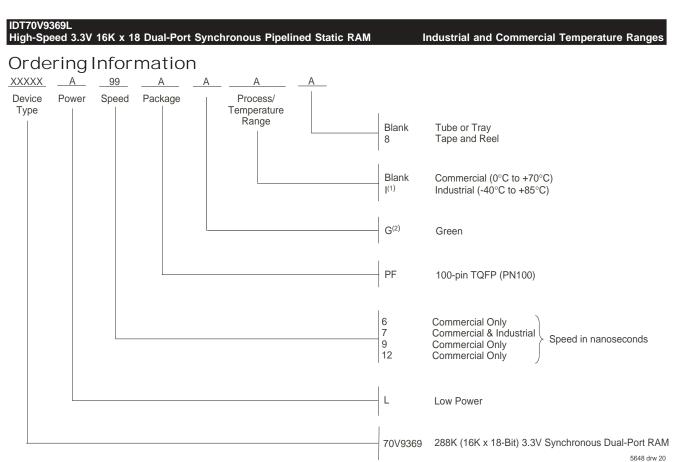
 $\overline{CE}_0 = VIL$ and $CE_1 = VIH$ for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9369's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{CE}_0 = VIL$ and $CE_1 = VIH$ to re-activate the outputs.

Depth and Width Expansion

The IDT70V9369 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the varioius chip enables in order to expand two devices in depth.

The IDT70V9369 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 36-bit or wider applications.





NOTES:

1. Contact your local sales office for industrial temp range for other speeds, packages and powers.

2. Green parts available. For specific speeds, packages and powers contact your sales office. LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02

Datasheet Document History

01/08/02:		Initial Public Release
10/11/04:		Removed "Preliminary" status
	Page 4	Updated Truth Table I
	0	Updated Absolute Maximum Ratings
		Updated Capacitance table
	Page 5	Added 6ns speed grade and 7ns I-temp, removed 9ns I-temp and updated DC power numbers
		in the DC Electrical Characteristics Table
	Page 7	Added 6ns speed grade and 7ns I-temp and removed 9ns I-temp AC timing numbers
		from the AC Electrical Characteristics Table
		Updated toe for 7ns and 9ns speed grades
	Page 9	Added Timing Waveform of Left Port Write to Pipelined Right Port Read
	Page 16	Added 6ns speed grade and 7ns I-temp and removed 9ns I-temp to ordering information
	Page 1 & 16	Replaced old TM logo with new TM logo
10/23/08:	Page 16	Removed "IDT" from orderable part number

Industrial and Commercial Temperature Ranges

Datasheet Document History (con't)

07/26/10:	Page 1	Added green parts availability to features
	Page 16	Added green indicator to ordering information
	Page 7	In order to correct the header notes of the AC Elect Chars Table and align them with the Industrial temp range values located in the table, the commercial TA header note has been removed
	Pages 8-12	In order to correct the footnotes of timing diagrams, CNTEN has been removed to reconcile the footnotes witht he CNTEN logic definition found in Truth Table II - Address Counter Control
06/20/15:	Page 2	Removed IDT in reference to fabrication
	Page 2	Removed date for the 100-PIN TQFP configuration
	Page 2 & 16	The package code PN100-1 changed to PN100 to match standard package codes
	Page 6	Corrected typo in the Typical Output Derating drawing
	Page 16	Added Tape and Reel indicator to Ordering Information
		Product Discontinuation Notice - PDN# SP-17-02
02/22/18:		Last time buy expires June 15, 2018

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